

深圳市晶泰源电子有限公司

JTY B772

TRANSISTOR(PNP)

FEATURES

Power dissipation

PCM:10W($T_{amb}=25^{\circ}C$)

Collector current

ICM:-3.0A

Collector-base voltage

V(BR)CBO: -40V

Operating and storage junction temperature range

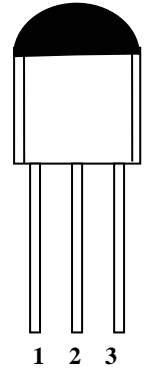
T_J, T_{stg} : $-65^{\circ}C$ to $-150^{\circ}C$

T0-92

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}C$ unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	$I_C=-1mA, I_E=0$	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	$I_C=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	V(BR)EBO	$I_C=-1mA, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.5	μA
Collector cut-off current	I_{CE0}	$V_{CE}=-30V, I_B=0$			-1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	H_{FE}	$V_{CE}=-5V, I_C=-1mA$	200		400	
Collector-emitter saturation voltage	VCE(sat)	$I_C=-2A, I_B=-200mA$			-0.5	V
Base-emitter saturation voltage	VBE(sat)	$I_C=-2A, I_B=-200mA$			-2.0	V
Transition frequency	f_T	$V_{CE}=10V,$ $I_C=50mA$ $f=30MHZ$	50			MHZ

CLASSIFICATION OF $h_{FE}(2)$

Rank	P	
Range	300-400	

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